SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

ABSTRACT OF THE DISCLOSURE

A method of realizing an active matrix display device having flexibility is provided. Further, a method for reducing parasitic capacitance between wirings formed on different layers is provided. After fixing a second substrate to a thin film device formed on a first substrate by bonding, the first substrate is removed, and wirings and the like are formed in the thin film device. The second substrate is removed next, and an active matrix display device having flexibility is formed. Further, parasitic capacitance can be reduced by forming wirings, after removing the first substrate, on the side in which a gate electrode over an active layer is not formed.

(Fig. 1)